

Product Overview

FDMQ8203: Dual N-Channel and Dual P-Channel PowerTrench® MOSFET, GreenBridge™ Series of High-Efficiency Bridge Rectifiers

For complete documentation, see the data sheet.

This quad mosfet solution provides ten-fold improvement in power dissipation over diode bridge.

Features

- Q1/Q4: N-Channel Max $r_{DS(on)} = 110 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$ Max $r_{DS(on)} = 175 \text{ m}\Omega$ at $V_{GS} = 6 \text{ V}$, $I_D = 2.4 \text{ A}$
- Substantial efficiency benefit in PD solutions
- Q2/Q3: P-Channel Max $r_{DS(on)} = 190 \text{ m}\Omega$ at $V_{GS} = -10 \text{ V}$, $I_D = -2.3 \text{ A}$ Max $r_{DS(on)} = 235 \text{ m}\Omega$ at $V_{GS} = -4.5 \text{ V}$, $I_D = -2.1 \text{ A}$
- RoHS Compliant

Applications

- Central Office

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(BR)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5 \text{ V}$ (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5 \text{ V}$ (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 10 \text{ V}$ (m Ω)	Q_g Typ @ $V_{GS} = 4.5 \text{ V}$ (nC)	Q_g Typ @ $V_{GS} = 10 \text{ V}$ (nC)	C_{iss} Typ (pF)	Package Type
FDMQ8203	0.6952	Pb-free Halide free non AEC-Q and PPAP	Active	Complementary	Dual	± 100	± 20	Q1,Q4: 4.0, Q2,Q3: 3.0	N: 6.0, P: 6.0	Q1: 22, Q2: 37	-	-	N: 110, P: 190	-	6.4	Q1/Q4: 158, Q2/Q3: 639	WDF N-12

For more information please contact your local sales support at www.onsemi.com.

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